Fabrication and Electrical Characterization of Near Ideal (n=1.1) Schottky Barrier Diodes of Au on n-GaSb

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1. Introduction

Among the III-V compound semiconductors, GaSb which is potentially important material for IR sources and detectors) is least studied material and there exist few reports on the electrical properties of schottky diodes of this material2-6). It has been suggested in past that schottky diode of Au on n-GaSb have barrier height (\(\Phi_B\)) 0.6eV and does not follow well known "two-third \(E_g\)" rule). However this \(\Phi_B\) value is based on C-V measurements, which can be modified considerably by interfacial layers. Richardson plot with ideality factor close to unity, which can determine \(\Phi_B\) more accurately, has not been reported so far for Au-GaSb schottky diodes. Recently n2 for Au schottky contacts on UHV and air cleaved GaSb has been reported8) which shows "effective barrier height" (0.49-0.52eV) obtained by curve fitting procedure. This may be partly because GaSb has high rate of oxidation in atmosphere which results in a thick oxide layer between metal and semiconductor. In presence of an oxide layer, the ideality factor of the diode generally turns out to be large and it is difficult to use thermionic-emission model to obtain \(\Phi_B\) from I-V measurements. Therefore fabrication of near ideal schottky contact is of much importance for our understanding of device properties. In the present work, we for the first time report fabrication of schottky diodes with ideality factor n=1.1. I-V and C-V measurements show that barrier height of Au on n-GaSb follows 2/3\(E_g\) rule.

2. Sample Preparation

The materials used is this work were grown by LPE on (100) n+ type GaSb substrates at about 500°C9). Te was used as n-type dopant to obtain carrier concentration of about 3.5x10¹⁶ cm⁻³.

For the fabrication of schottky barrier diodes, we first investigated conditions for surface preparation of GaSb before forming the schottky contact and found it to be somewhat critical due to high oxidation rate of GaSb in atmosphere10). Following procedure

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resulted in fabrication of diodes with ideality factor n=1.1: A back contact of Au-Ge-Ni is alloyed to n⁺ substrate of LPE n-GaSb. Organically cleaned sample is oxidized in water and etched in dilute HCl several times. Finally the sample is etched in a mixture of HF and H₂O. It is then briefly rinsed in DI water, dried in the folds of clean filter paper and quickly loaded into the vacuum chamber. This last step is critical and in order to ensure better ideality factor, the exposure of each cleaned sample to water and air atmosphere is minimized to less than 1 minute. Before evaporating the metal, sample is first desorbed by heating to ~125°C and then cooled back to room temperature to avoid interdiffusion of constituent at the surface. Then Au is evaporated through a glass mask containing holes of 400μm diameter to form metal semiconductor contact. Sample is now ready for electrical measurements.

3. Characterization

3.1. C-V Characteristics

1MHz C-V measurements were carried out over a temperature range 180-370K (Fig.1) and barrier heights as a function of temperatures (Fig.2) were obtained by using the analysis in Ref.11. From Fig.2 we obtain Φ_B(0)=0.66eV and slope of the curve gives a value of α=6.6x10⁻⁴eV/K and Φ_B(300K)=0.47eV.

3.2. I-V Characteristics

Current-voltage measurements performed at several temperatures are shown in Fig.3 (lnI vs V plot). The ideality factor obtained from these curves is nearly 1.2 at room temperature. It improves to and saturates to a value of 1.1 in the temperature range 340-370K. At lower temperature ideality factor worsens (Fig.4). We consider the limiting value of n to be the result of a remnant interfacial layer as given by Rhoderick\(^{12}\)

\[
n = 1 + \frac{\delta}{\varepsilon_1} \left[ \frac{\varepsilon_S}{W} + \sum D_{sa} \right] \frac{1 + \frac{\delta}{\varepsilon_1} q^2 D_{sb}}{1 + \frac{\delta}{\varepsilon_1} q^2 D_{sa}}
\]

where \(D_{sa}\) and \(D_{sb}\) are densities of interface states which are in equilibrium with metal Fermi level and semiconductor Fermi level. For n=1.1 we find values of \(\delta=25\alpha\), \(D_{sa}=1\times10^{13}\) cm⁻²eV⁻¹ and \(D_{sb}=2\times10^{12}\) cm⁻²eV⁻¹.

In the regime of ideality factor n=1.1, Richardson plot \(\ln I_0/T^2\) vs 1000/T is linear (Fig.5) and hence we apply thermionic emission theory to determine barrier height\(^7\)

\[
I_0(T) = S A T^2 \exp \left( -\frac{\Phi_B}{kT} \right) \exp(-\alpha T^{1/2})
\]
3.3. Discussions

Analysis of I-V and C-V data shows that the value of $\Phi_B'(0)$ determined from C-V measurements is considerably larger than the value of $\Phi_B'(0)$ determined from I-V measurements. This difference can be attributed to the presence of interfacial layer $\delta$ in which

$$\Delta = \Phi_B(C-V) - \Phi_B(I-V) = \nu V_D + V_1^{1/2} D_D^{1/2} + \frac{1}{4} V_1^{1/4}$$

where $\nu = \frac{\Phi_{D_s}^{3/2} D_{sb} \delta^2}{\varepsilon_i^2}$ and $V_1 = 2\varepsilon_s N_{D_s} \frac{\delta^2}{\varepsilon_i^2}$.

Therefore in the temperature range where the ideality factor $n$ and the difference in $\Phi_B$ values $\Delta$ is determined by the interfacial layer $\delta$, $D_{sa}$ and $D_{sb}$, we can estimate the value of $\Delta$ for values of $\delta$, $D_{sa}$, and $D_{sb}$ mentioned above. We found for $n=1.1$, $\Delta$ is 0.085eV which corresponds to a difference in the measured values of $\Phi_B|_{C-V}=0.66eV$ and $\Phi_B|_{I-V}=0.58eV$ at 0 K.

In our work, for the diodes with $n=1.1$ Richardson plot gives $\Phi_B(0)=0.58eV$. Using the value of $\alpha=6.8x10^{-4}eV/K$, $\Phi_B(300K)$ is found to be 0.39eV. It may be remarked however that the value of $\alpha$ for most semicon-
ductors lies between $3 \times 10^{-4} \text{eV/K}$. Therefore if we consider value of $n$ as $4 \times 10^{-4} \text{eV/K}$ then $\Phi_B(300\text{K})=0.46\text{eV}$ which is similar to $\Phi_B(300\text{K})=0.47\text{eV}$ obtained from C-V measurements for diodes with $n=1.1$. Now since the bandgap of GaSb is $E_g=0.70\text{eV}$ and $\Phi_B=0.46\text{eV}$ at 300K, we see that the schottky diodes of Au on n-GaSb follows "two-third $E_g$ rule".

Next, room temperature $\Phi_B$ obtained from C-V measurements by us for diodes having poor ideality factor ($n=2$) is $0.60\text{eV}$ which is close to the value of $0.61\text{eV}$ reported by Mead and Spitzes from C-V data, by Chin from room temperature I-V and photoemission techniques, and by Naga from I-V. None of these authors have reported values of $n$, which of prime importance in determination of $\Phi_B$. The value of $\Phi_B=0.61\text{eV}$ obtained by Chin, from internal photoemission at 300K is doubtful because the bandgap of GaSb, $E_g(300\text{K})=0.7\text{eV}$, is close to the measured value of barrier height, $\Phi_B=0.60\text{eV}$, the energy range for $\Phi_B$ determination from internal photoemission technique ($\Phi_B \leq \hbar \omega \leq E_g$) is small, the onset of electron-hole pair excitations across the bandgap for $h\omega \leq E_g$ will contribute to the photocurrent in the range of $\Phi_B$ measurements and this can cause serious error in the $\Phi_B$ value by this technique. Our results clearly indicates the lower value of $\Phi_B$ for near ideal schottky diodes measured from Richardson plots.

Next the increase in the value of $n$ at low temperature can be caused by different mechanisms. These includes i)generation recombination, ii)thermionic field emission, and iii)tunneling current. All these may contribute to the total observed current at a given bias. Our results of I-V measurements in reverse bias at different temperatures indicates that the current flow in high temperature region, $T>300\text{K}$, is dominated by thermionic-emission current and at low temperature $T<300\text{K}$ possibly by the thermionic field emission, both in the forward bias as well as reverse bias.

4. Conclusions

We can say that surface preparation of GaSb is very critical and we have been able to reproducibly fabricate diodes with ideality factor $n=1.1$ by optimizing surface preparation condition which minimizes the interfacial layer. The value of barrier height for diodes having $n=1.1$ is $0.46\text{eV}$ and follows "2/3$E_g$ rule".

Acknowledgements

One of the authors, P.A. Murawala, greatfully acknowledges kind supports received from Prof. Sg. Fujita and Dr. Sz. Fujita of Dept. of Electrical Eng., Kyoto University for preparation, critical reading, and publication of this manuscript. Thanks are also due to Mr. O. Tsuji, President of Samco International Inc. for his help and encouragement.

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